

Fig. 1A

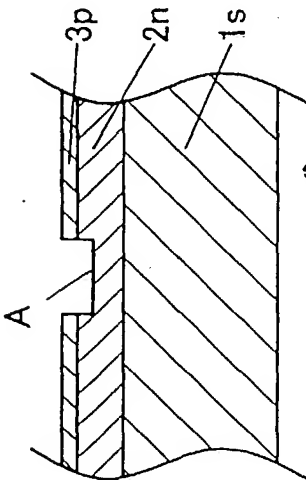


Fig. 1B



Fig. 1C

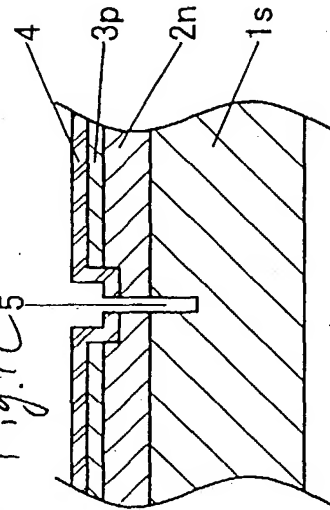


Fig. 1D

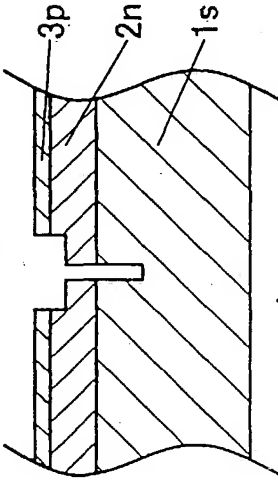


Fig. 1E

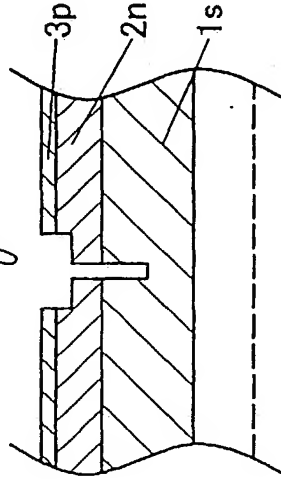


Fig. 1F

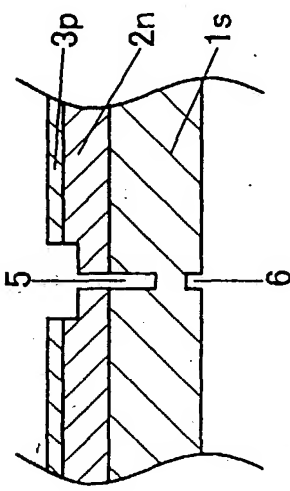


Fig. 1G

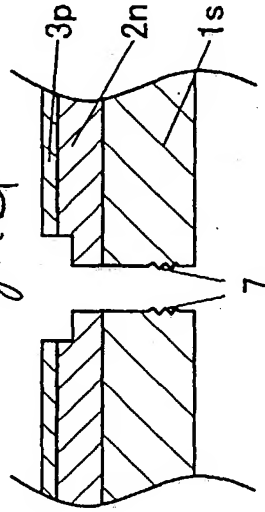


Fig. 2A

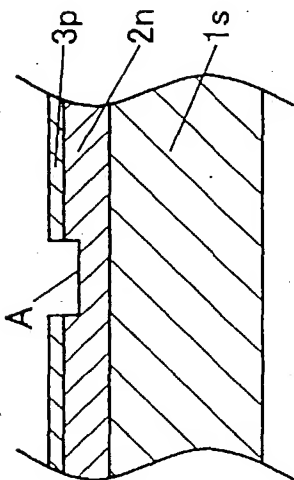


Fig. 2B

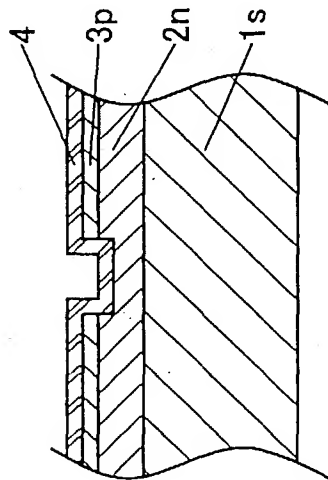


Fig. 2C

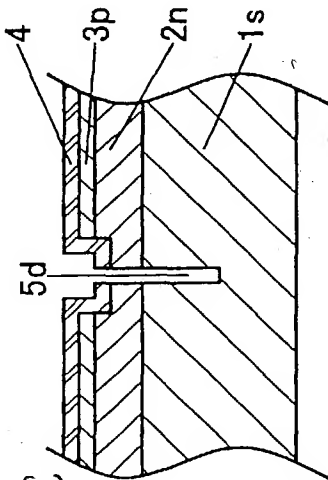


Fig. 2D

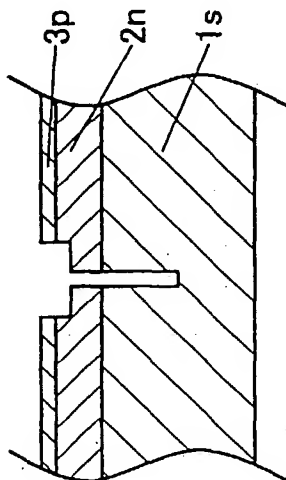


Fig. 2E

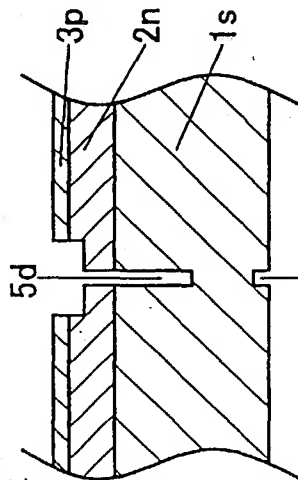


Fig. 2F

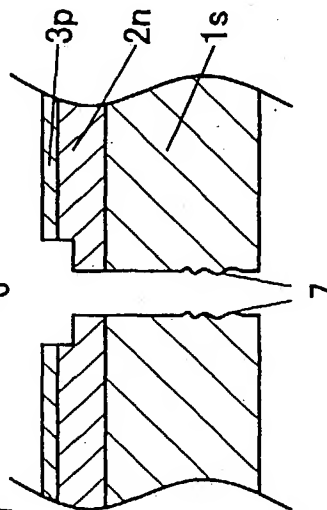


Fig. 3A

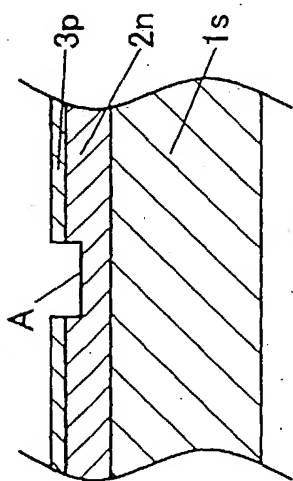


Fig. 3B

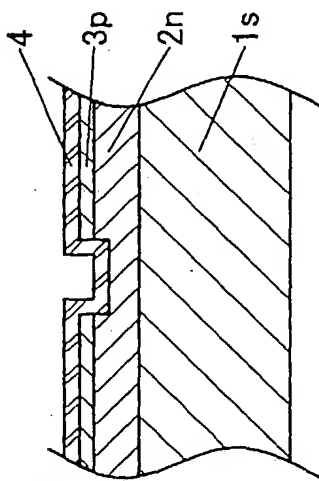


Fig. 3C

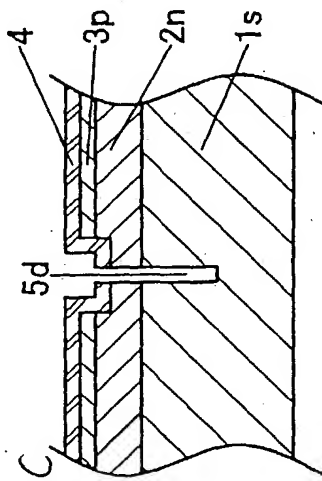


Fig. 3D

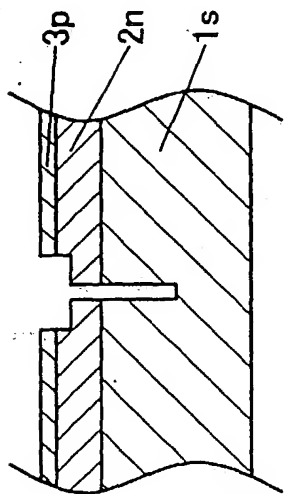


Fig. 3E

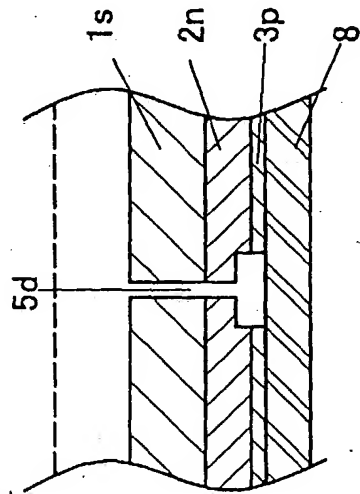


Fig. 3F

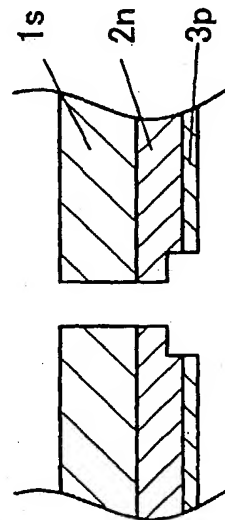


Fig. 4A

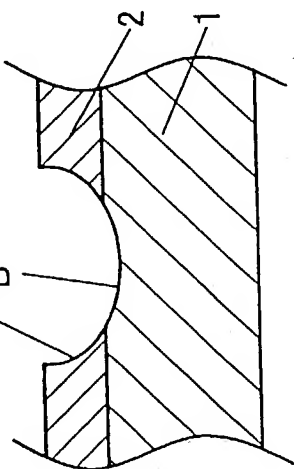


Fig. 4B

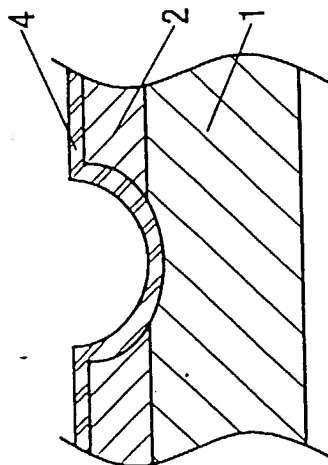


Fig. 4C

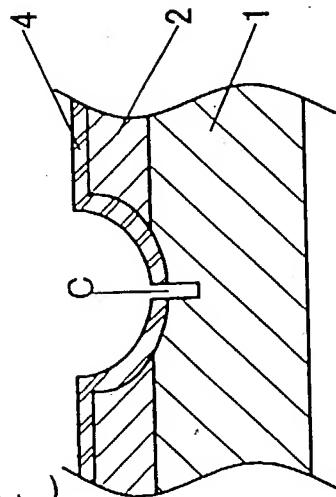


Fig. 4D

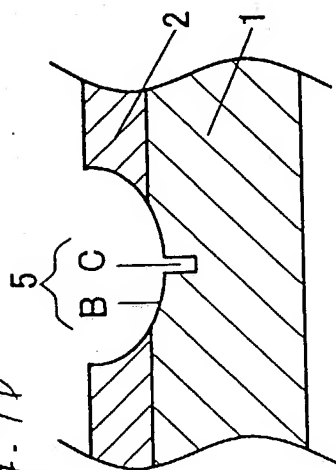


Fig. 4E

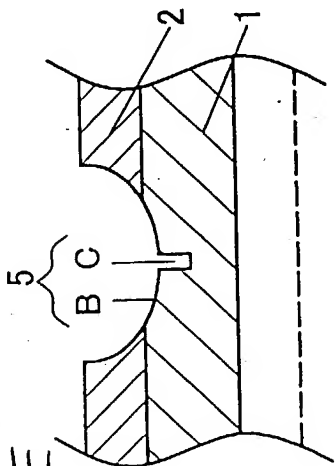


Fig. 4G

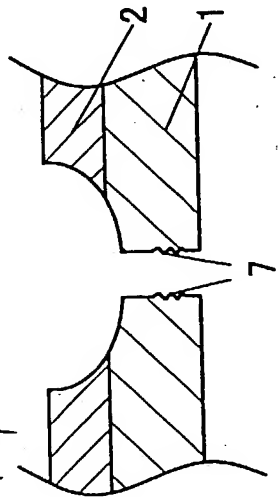


Fig. 4F

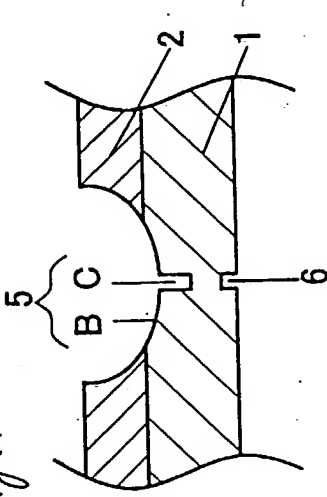


Fig. 5A

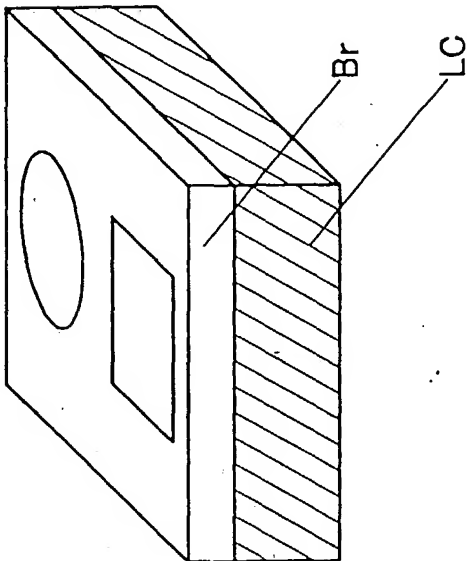


Fig. 5B

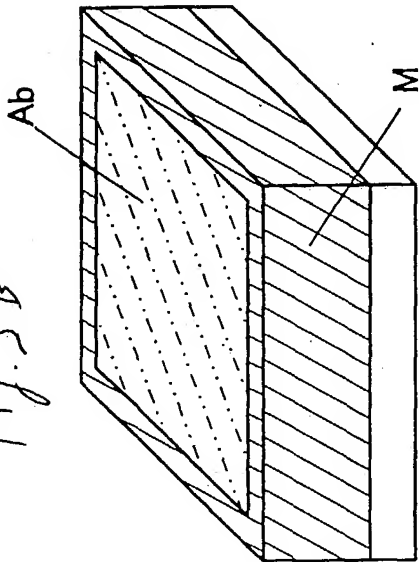


Fig. 5C

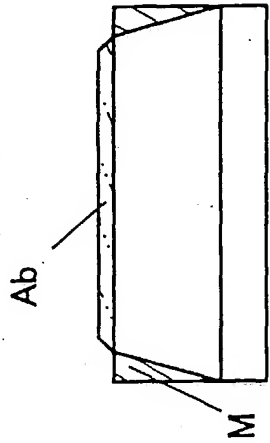


Fig. 5D

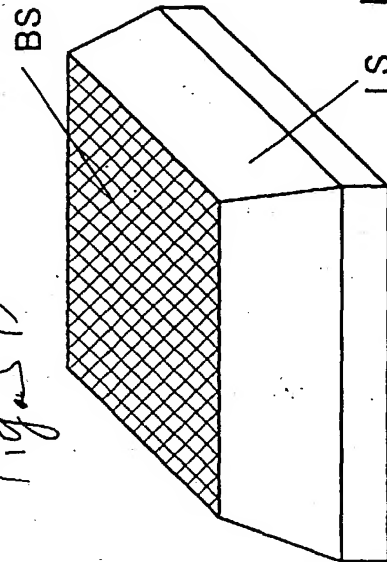
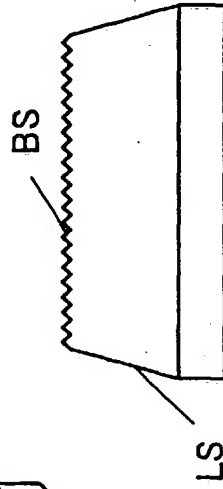


Fig. 5E



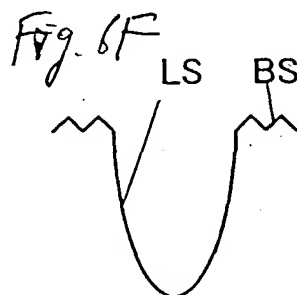
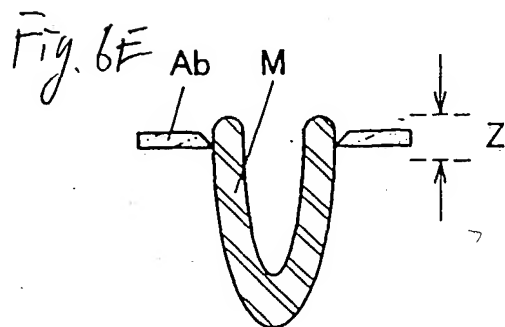
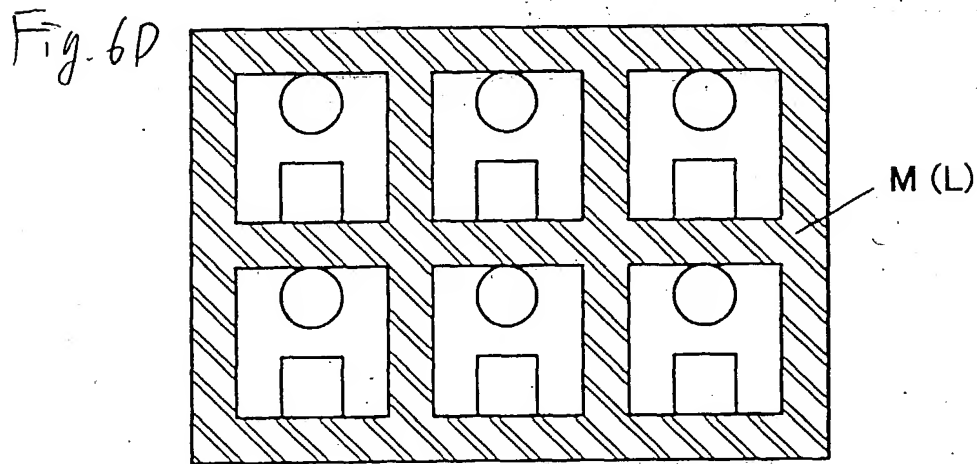
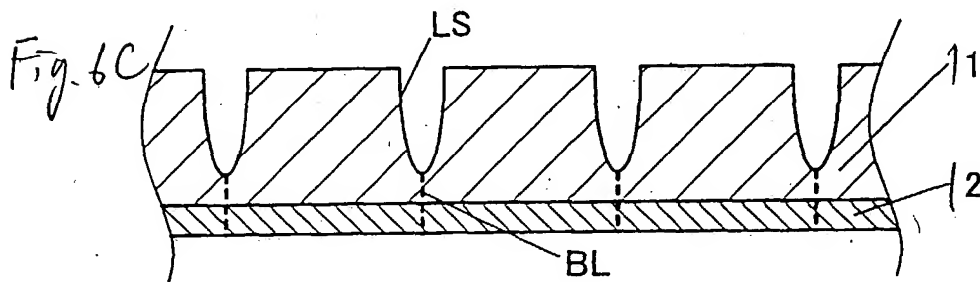
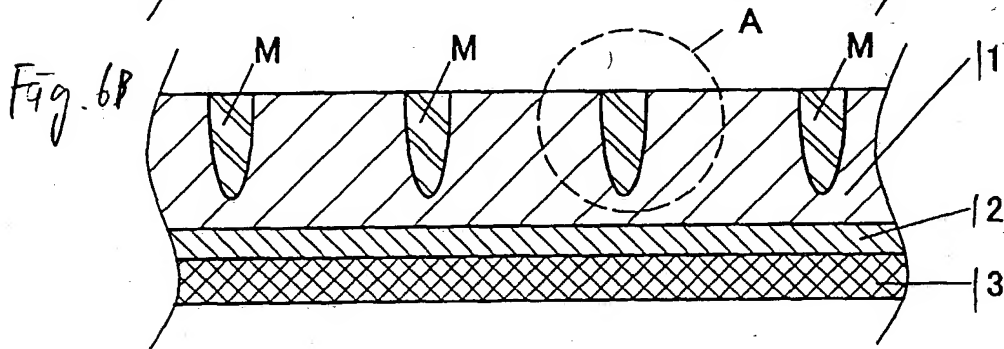
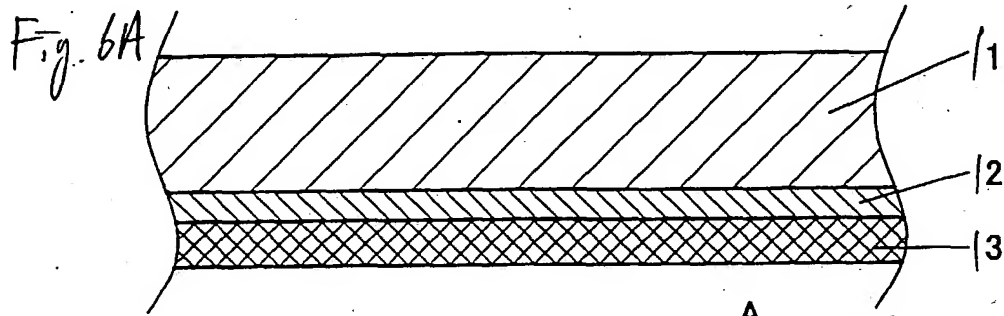


Fig. 7A

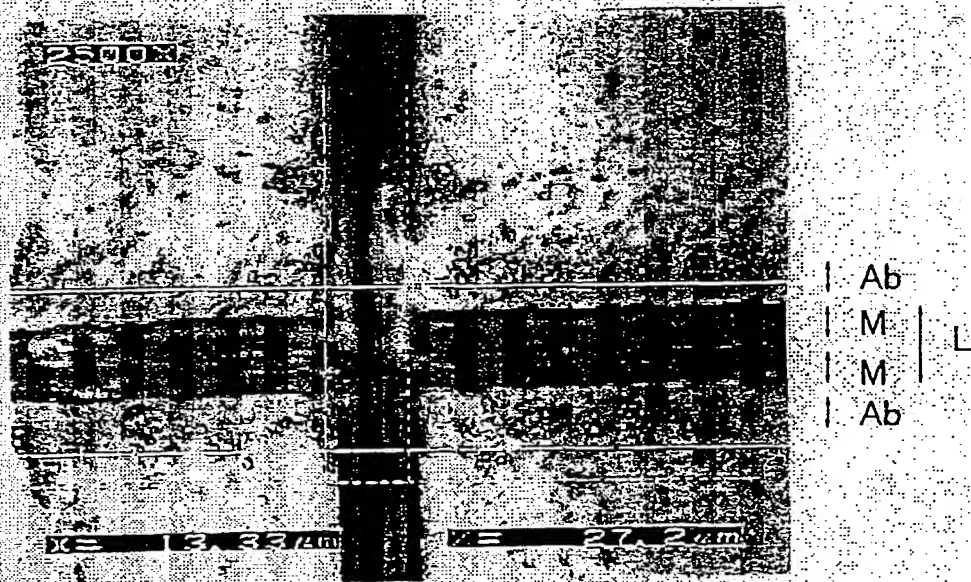


Fig. 7B

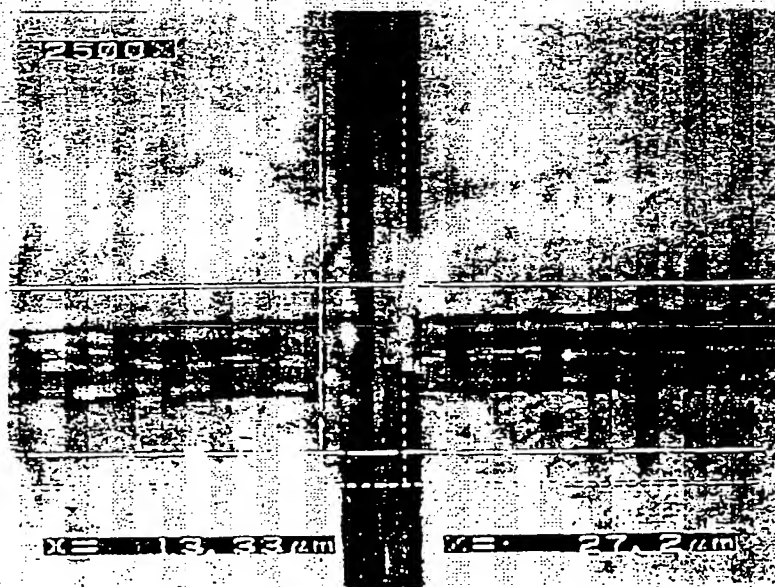


Fig. 8

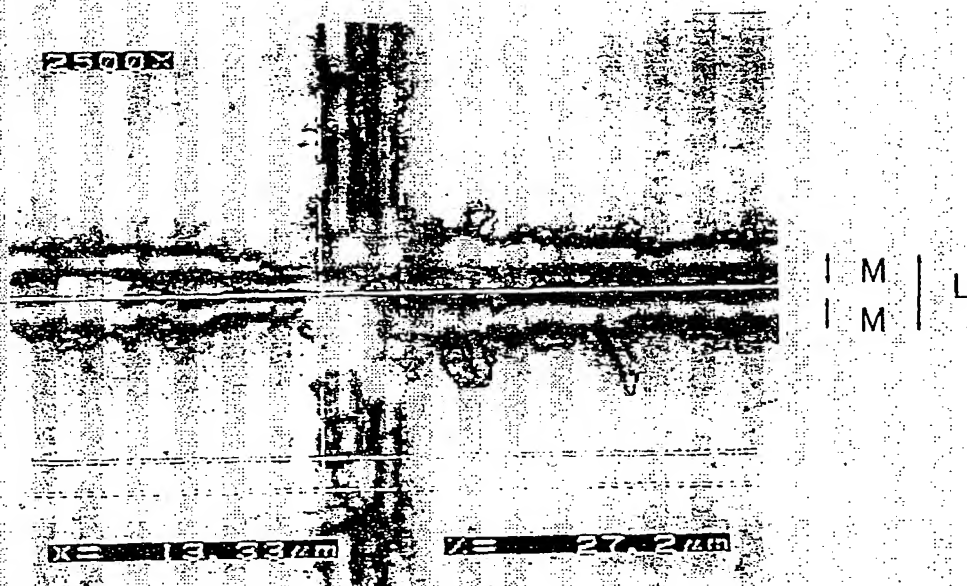


Fig. 9

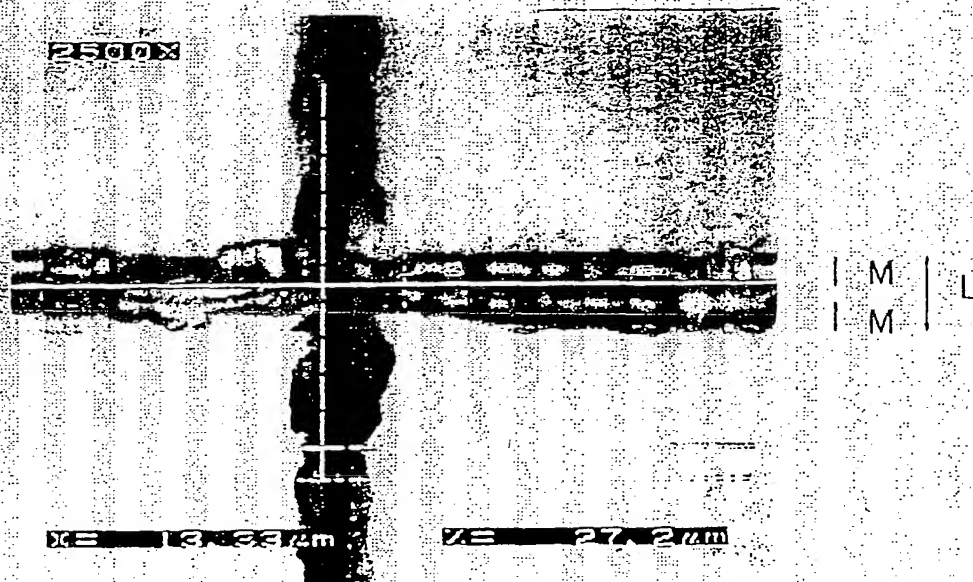




Fig. 10A

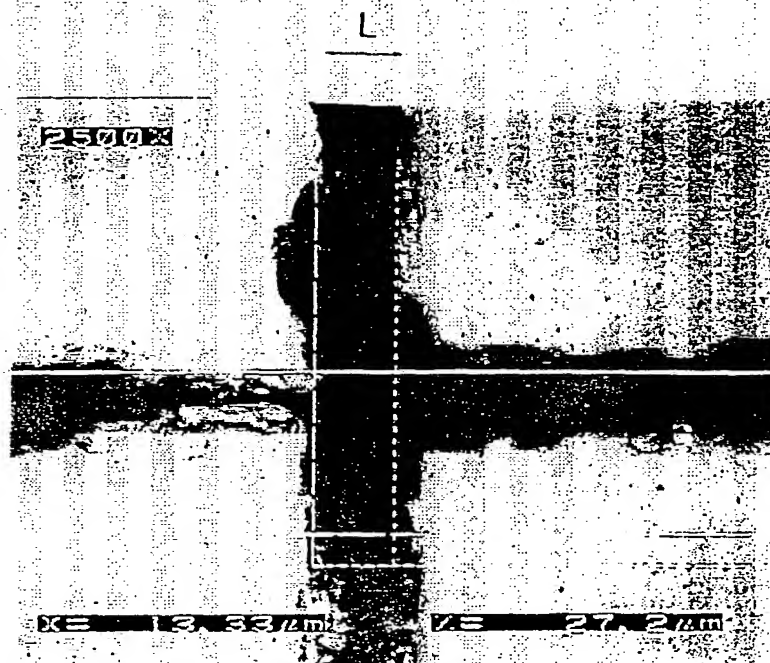


Fig. 10B

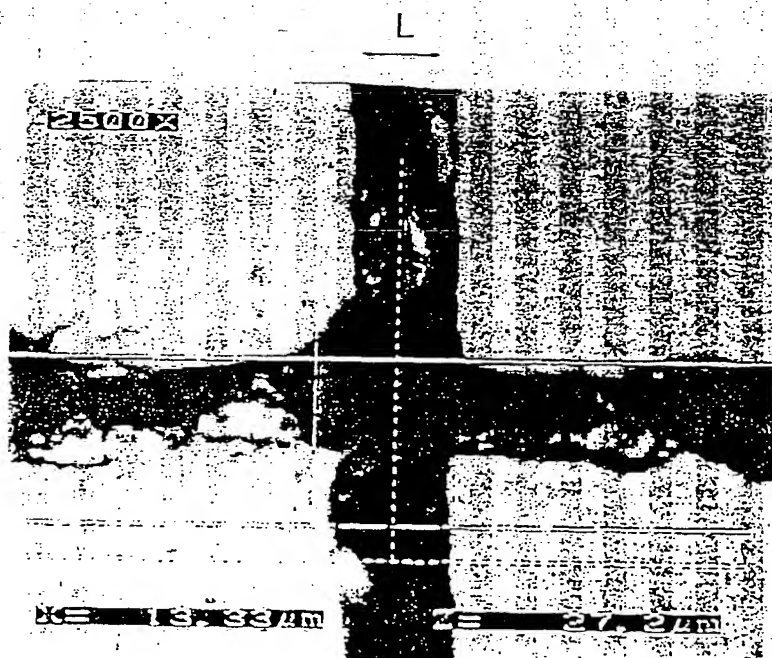


Fig. 11A

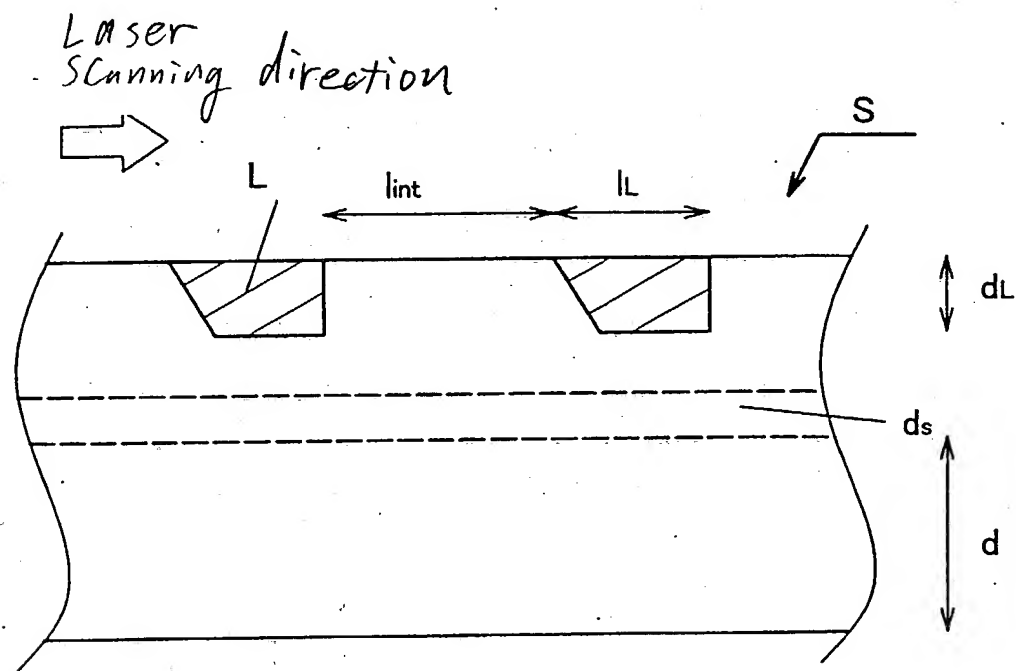


Fig. 11B

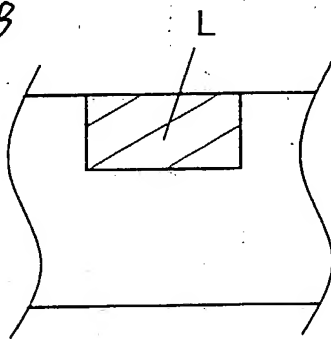


Fig. 11C

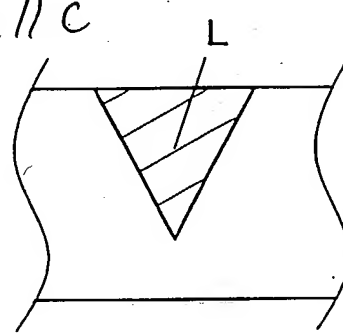


Fig. 11D

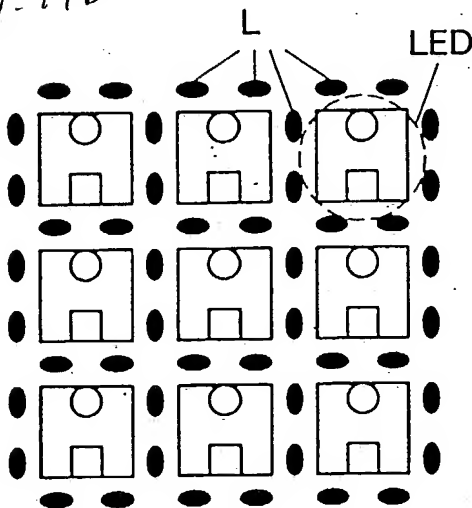


Fig. 11E

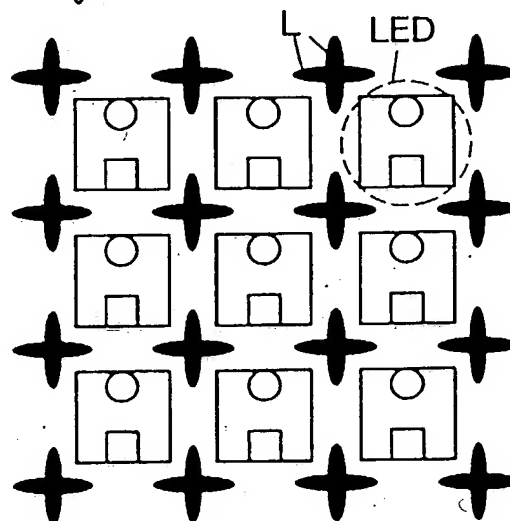


Fig. 12A

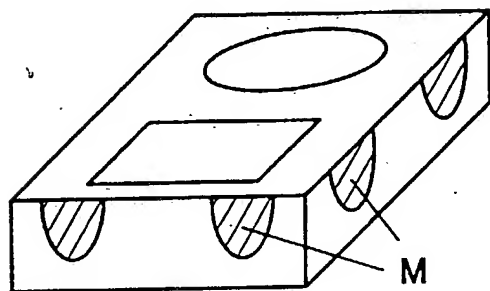


Fig. 12B

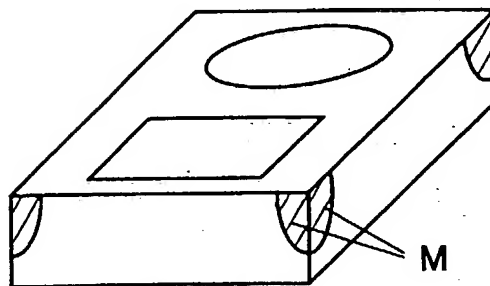


Fig. 13A

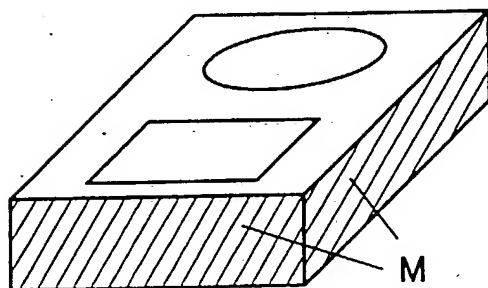


Fig. 13B

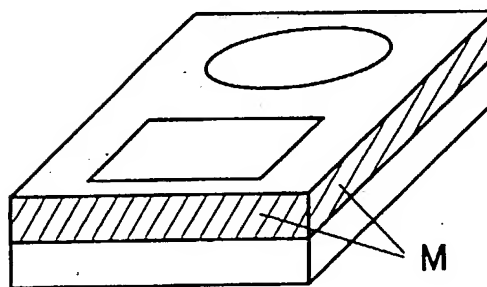


Fig. 14A

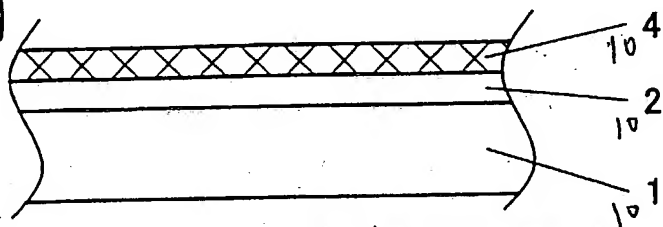


Fig. 14B

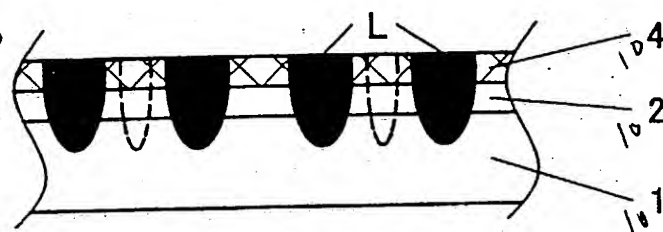


Fig. 14C

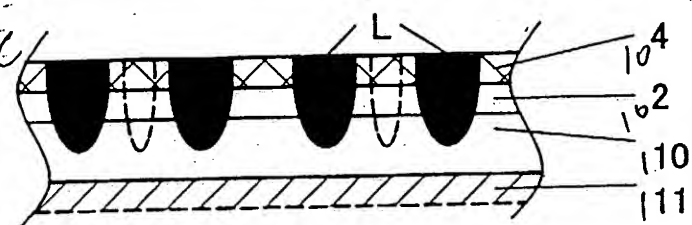


Fig. 14D

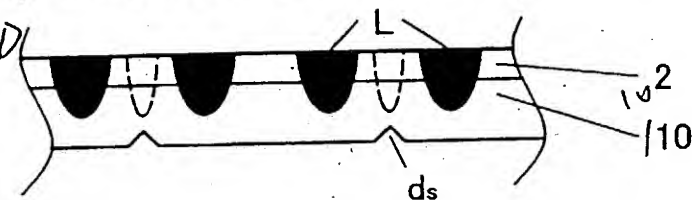


Fig. 15A

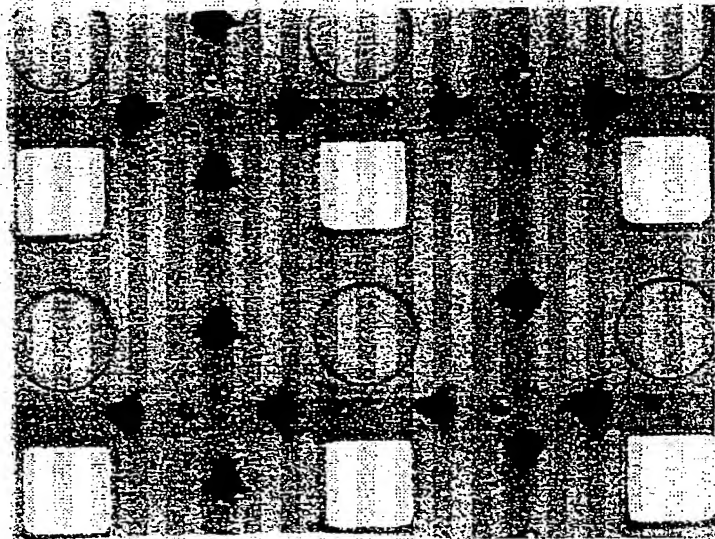


Fig. 15B

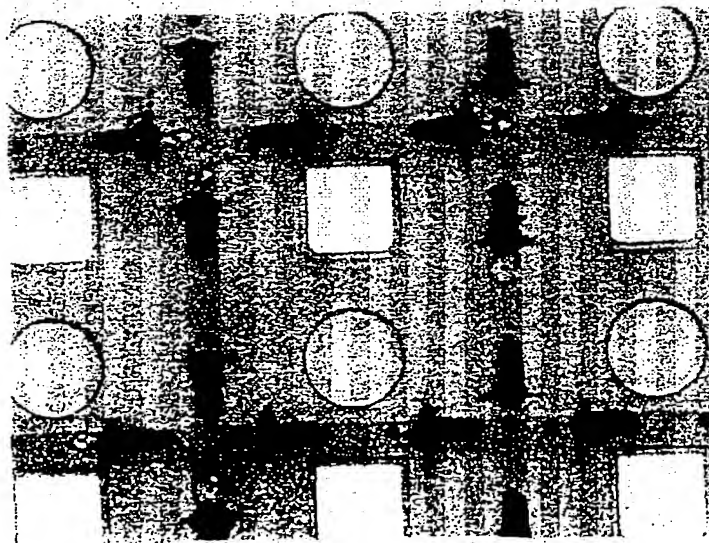


Fig. 16A

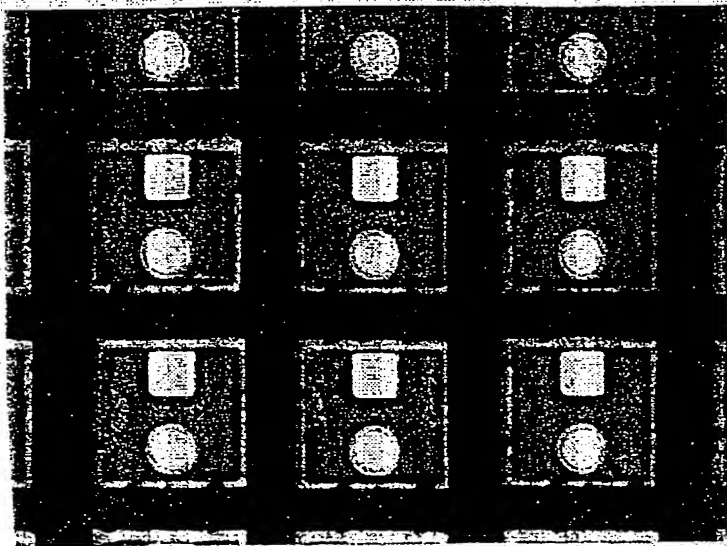


Fig. 16B

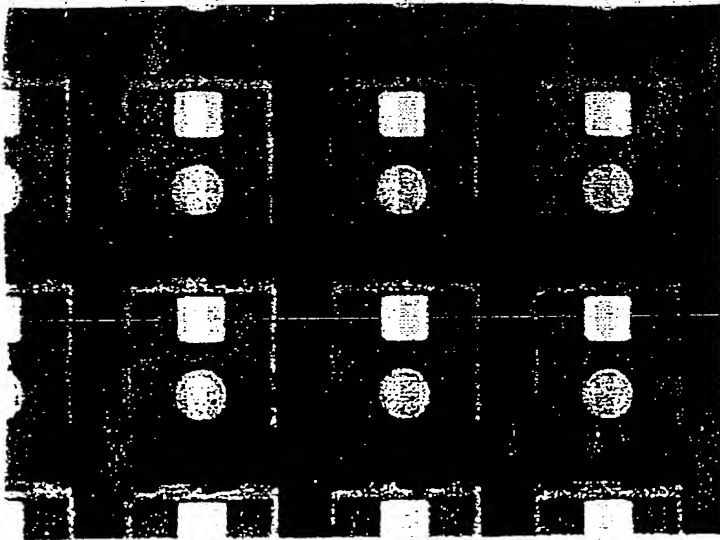


Fig. 17A

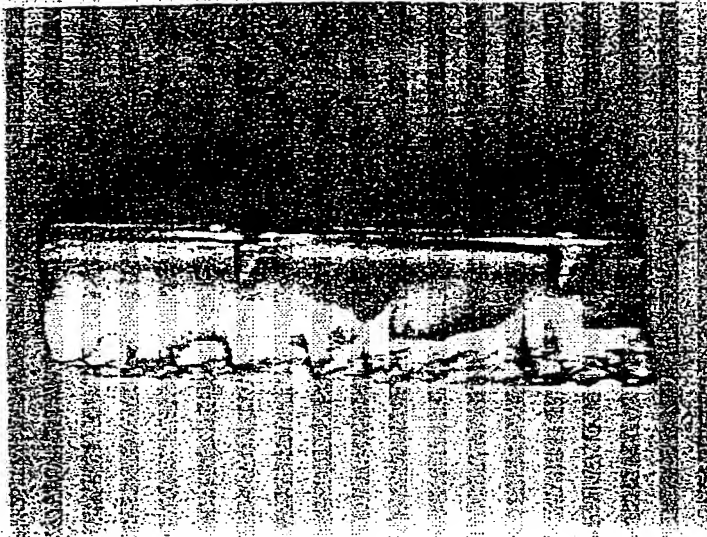


Fig. 17B

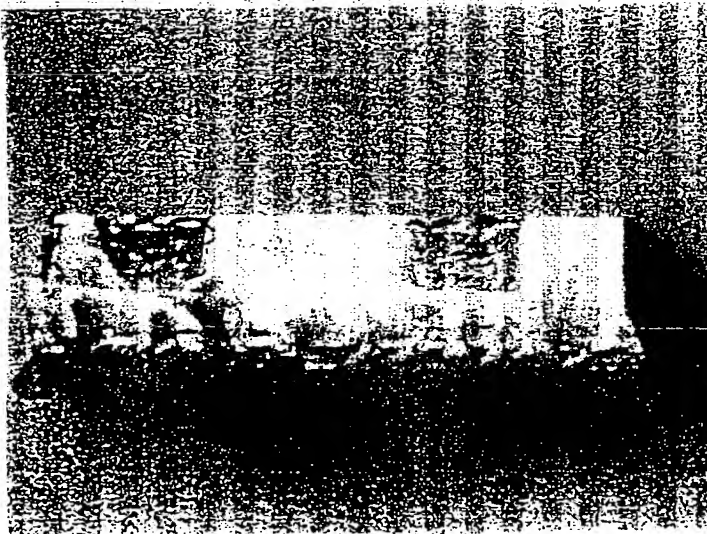


Fig. 18

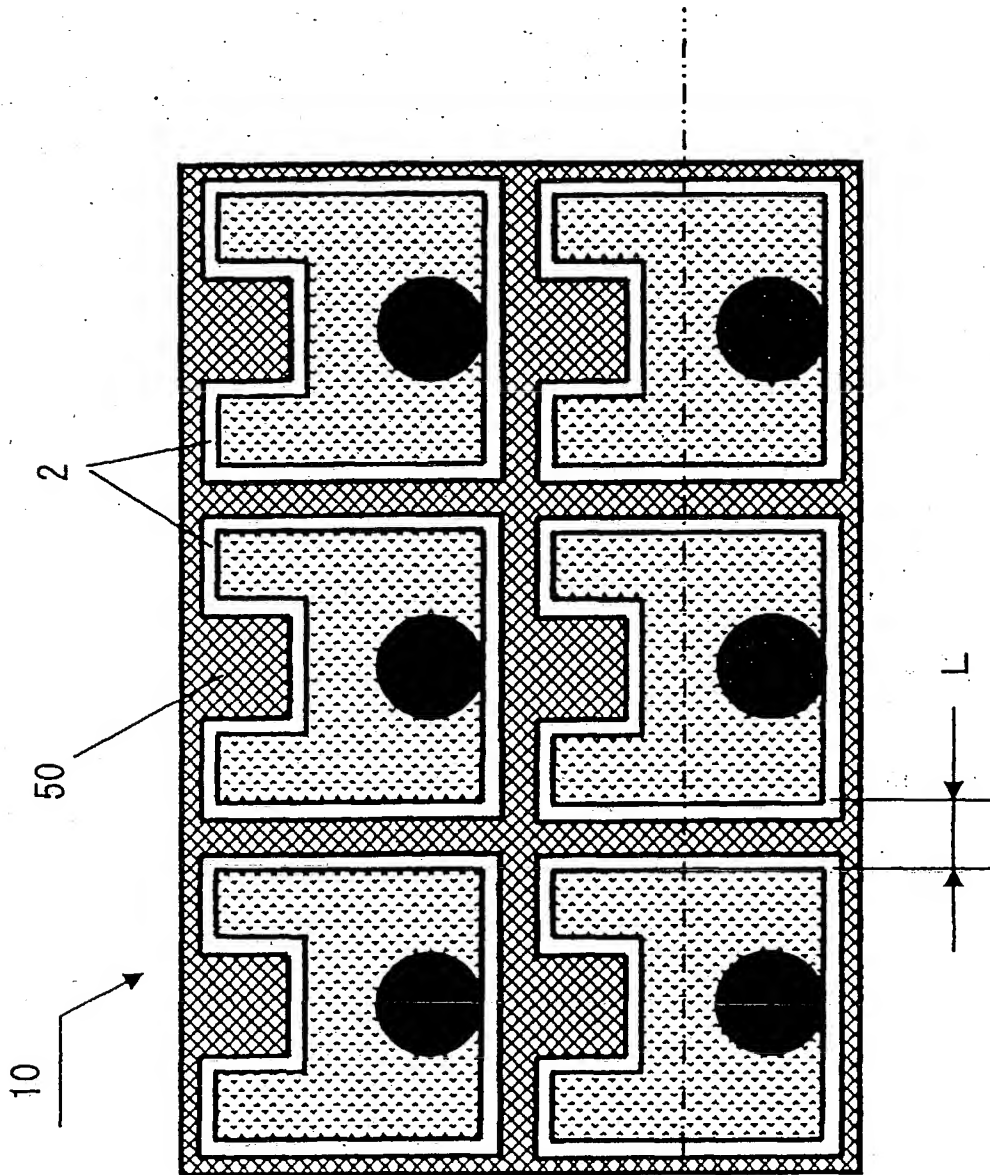




Fig. 19A

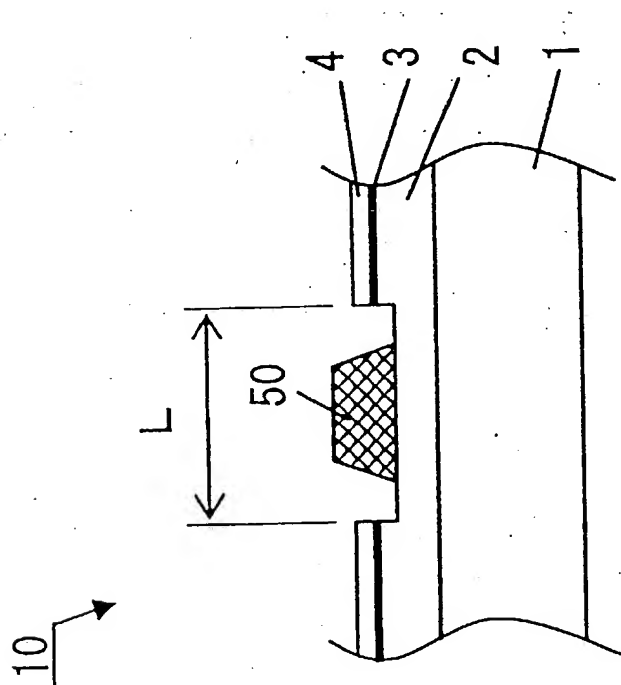


Fig. 19B

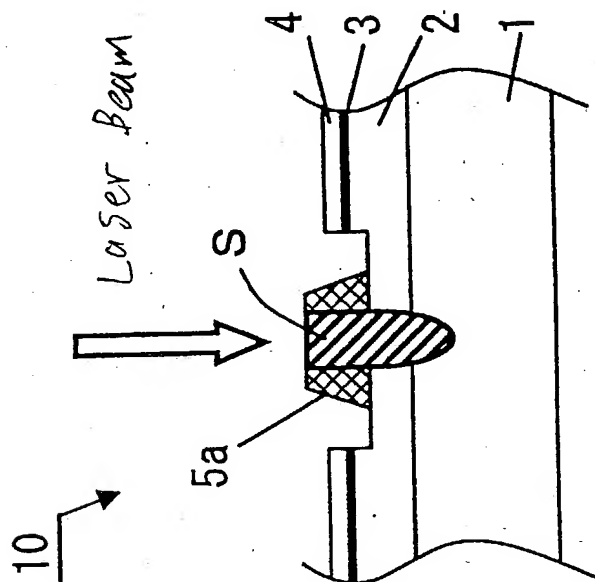
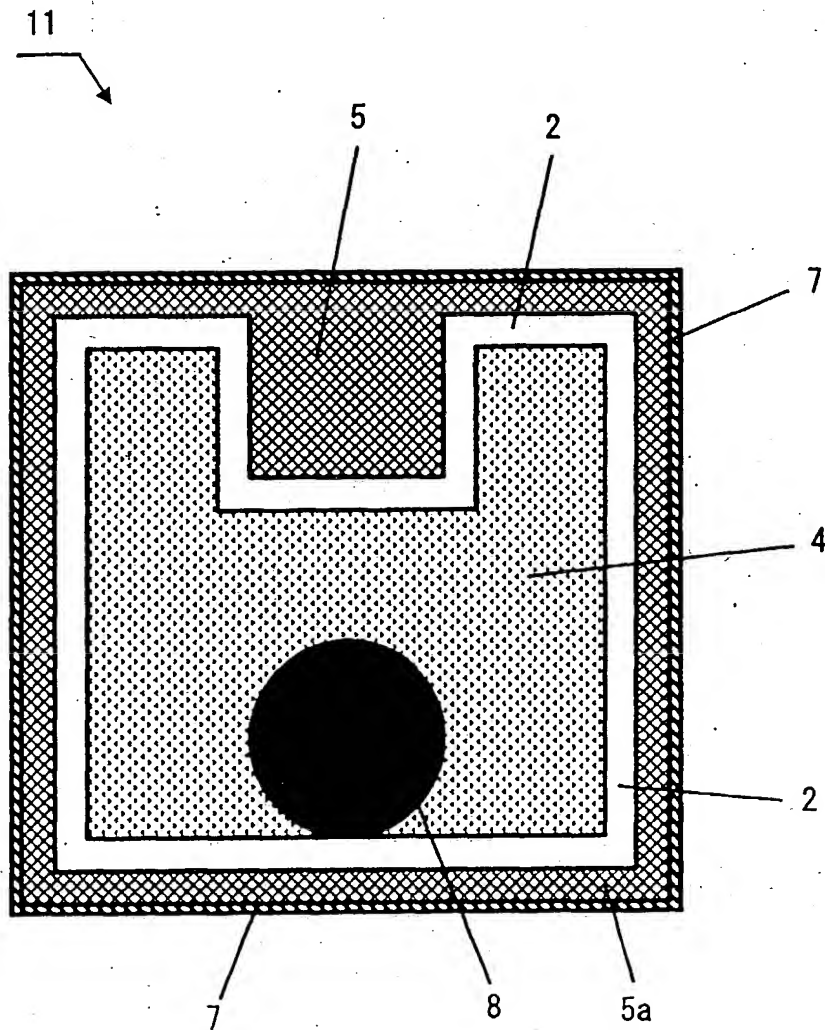


Fig. 20



A cross-sectional view of a semiconductor device. It features a central trench labeled 'S'. The trench is filled with a material indicated by a cross-hatch pattern. On either side of the trench, there are regions labeled '7' and '6', also filled with the cross-hatch material. Above these regions are layers labeled '4' and '3'. The entire structure is built on a substrate labeled '1' and '2'.

Fig. 22

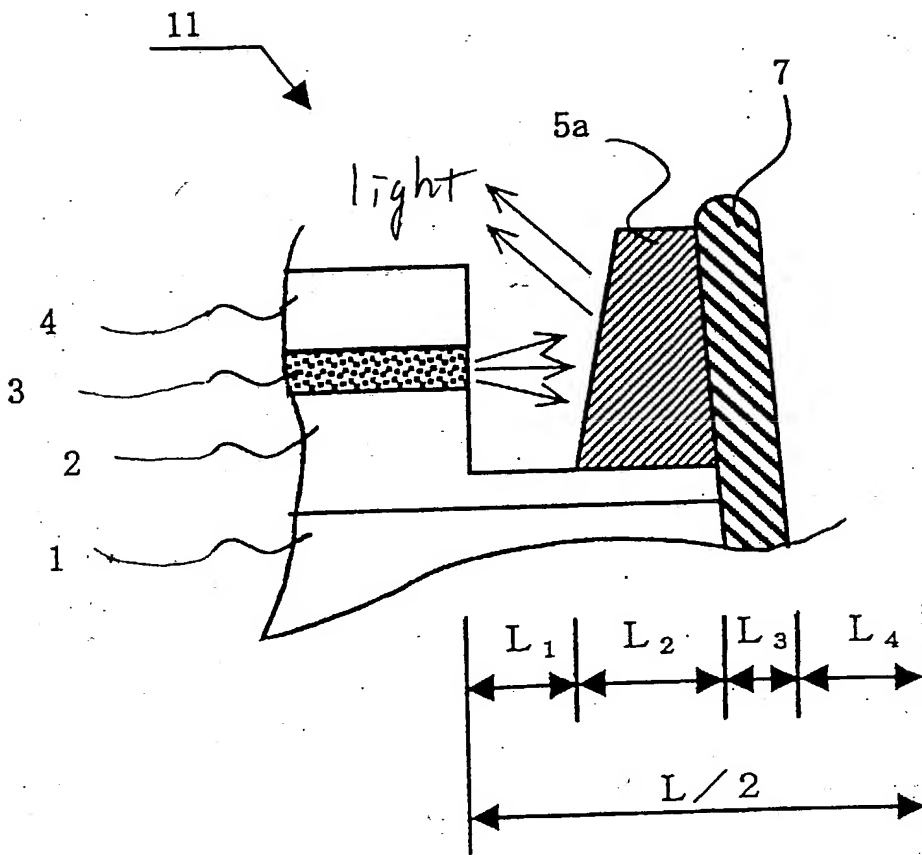


Fig. 23A

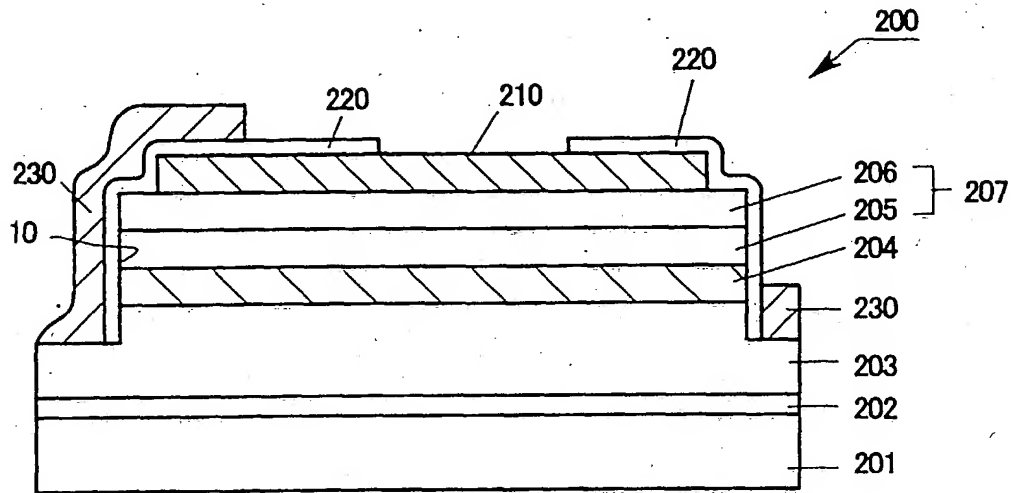


Fig. 23B

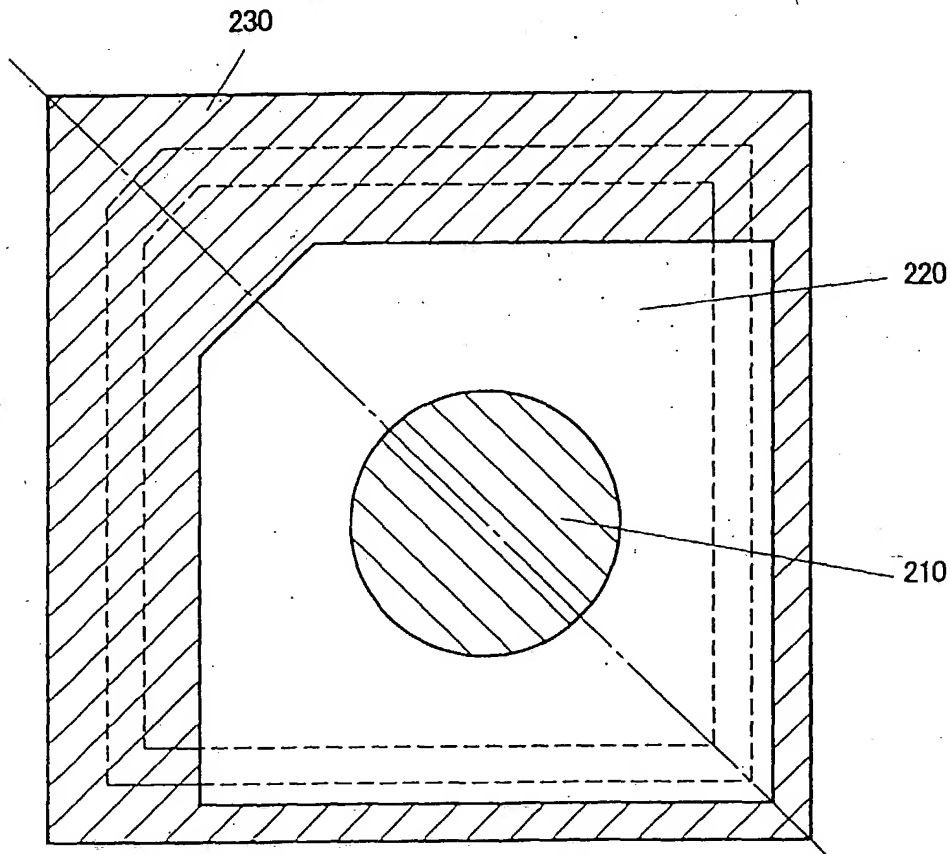


Fig. 24

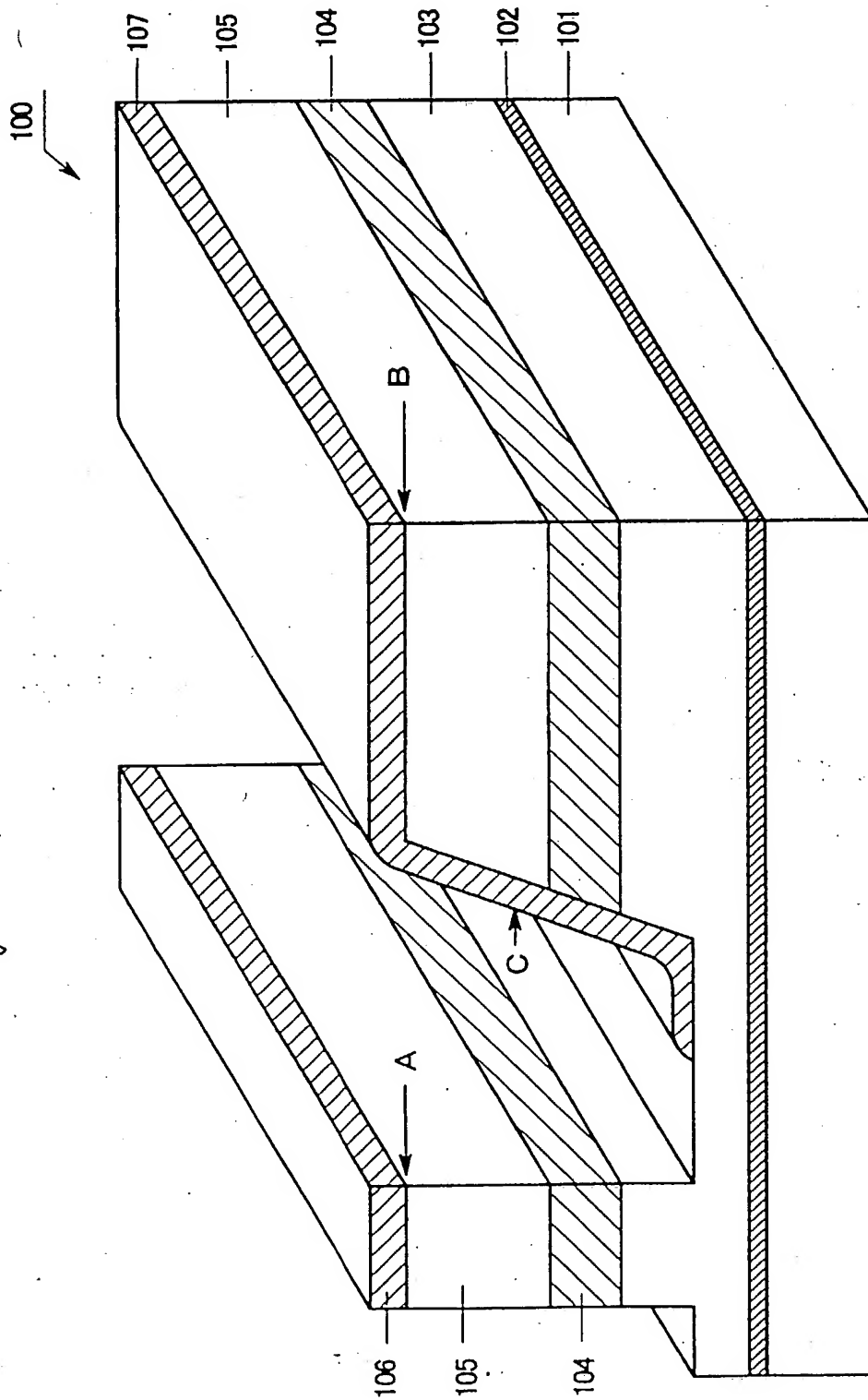


Fig-25A

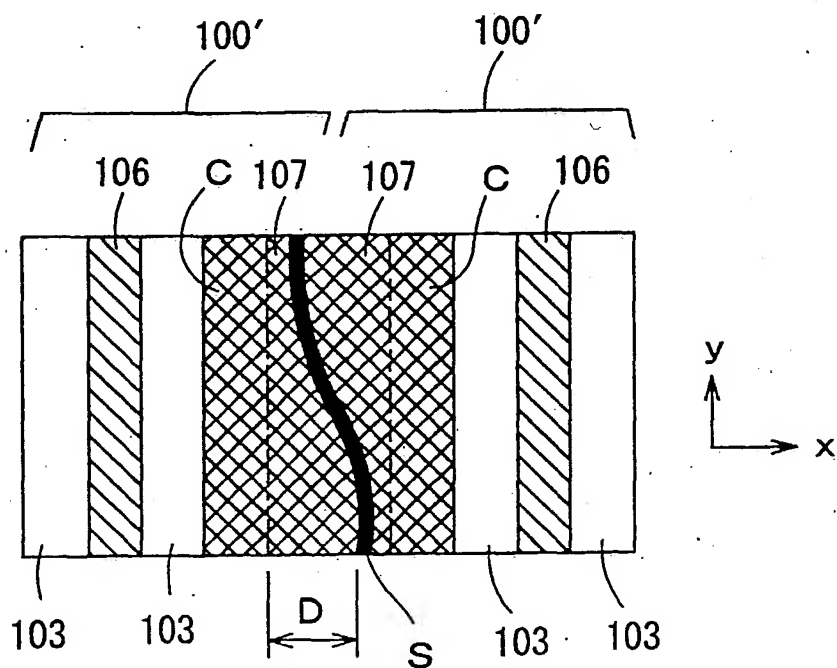


Fig-25B

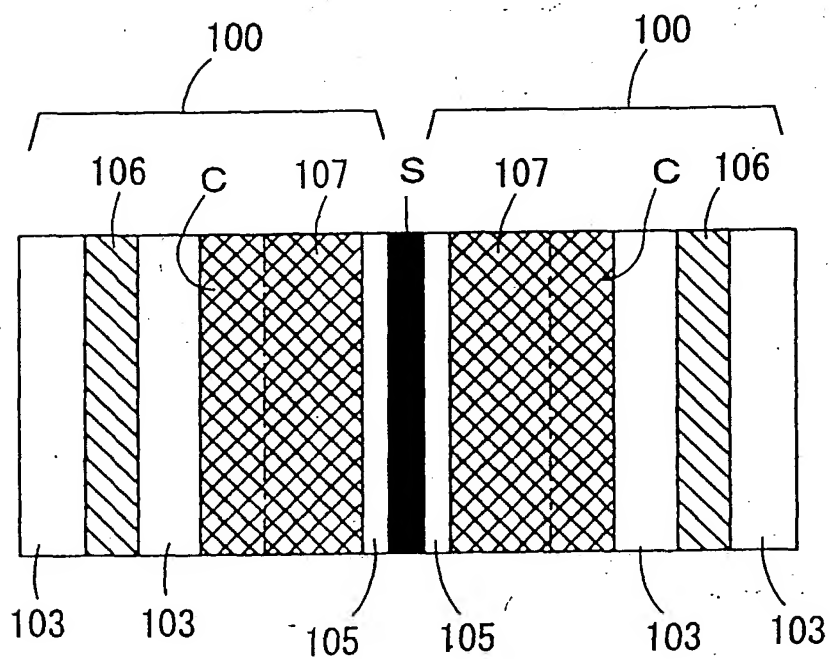


Fig. 26A

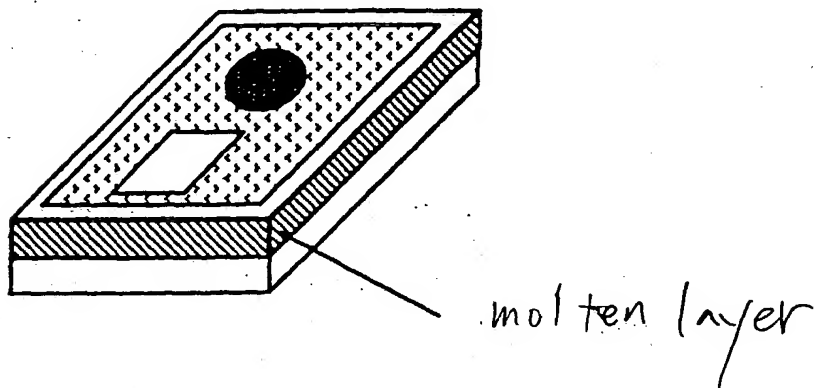


Fig. 26B

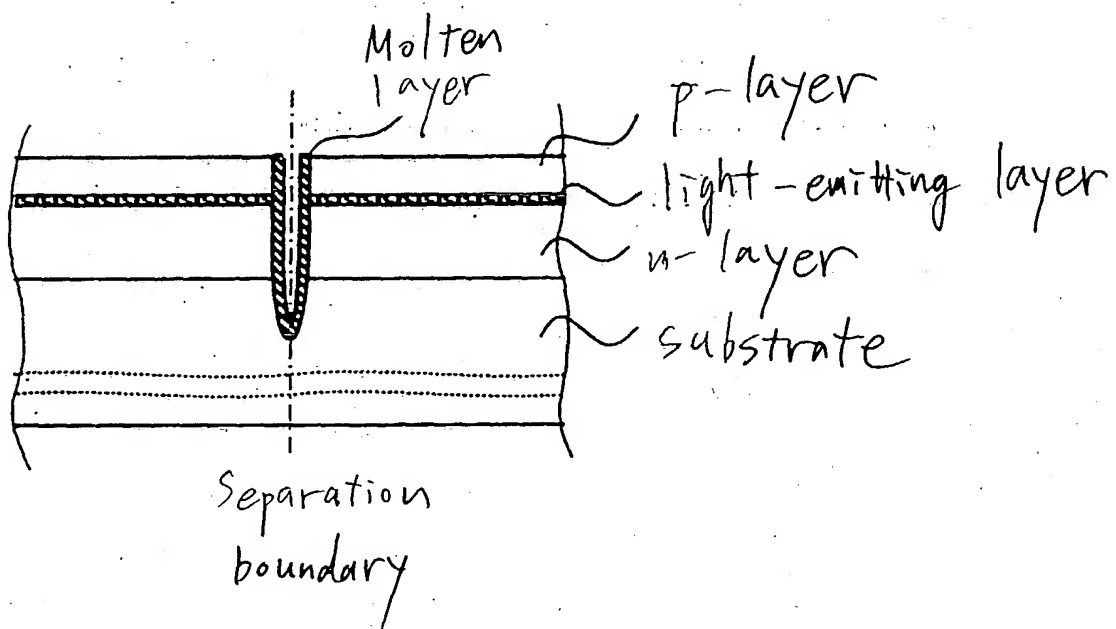




Fig. 29C

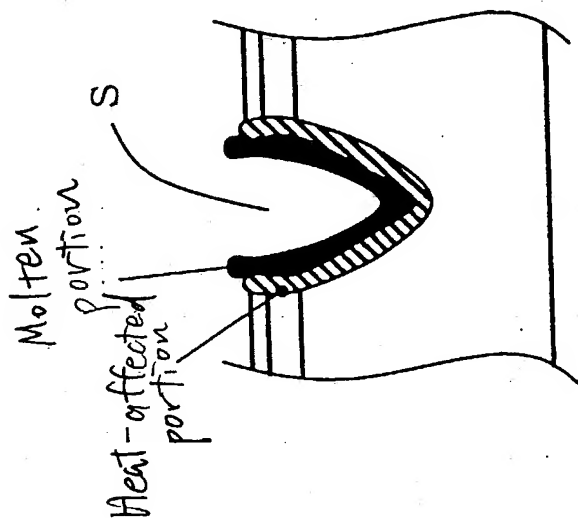


Fig. 29B

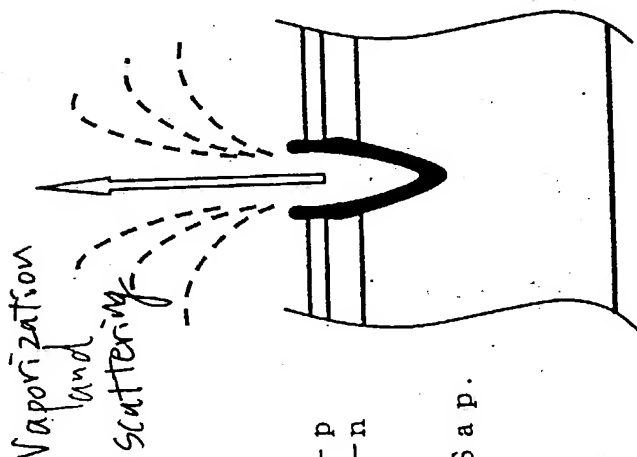


Fig. 29A

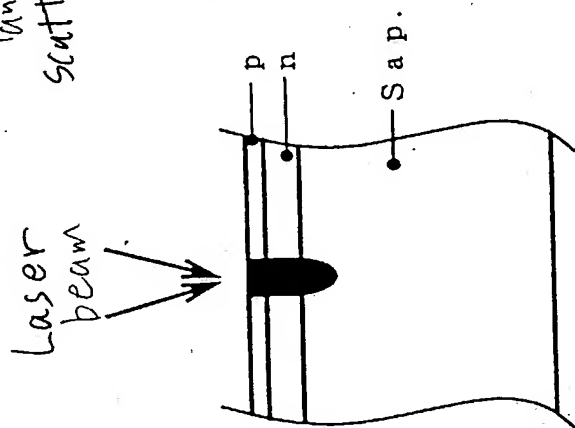


Fig. 28

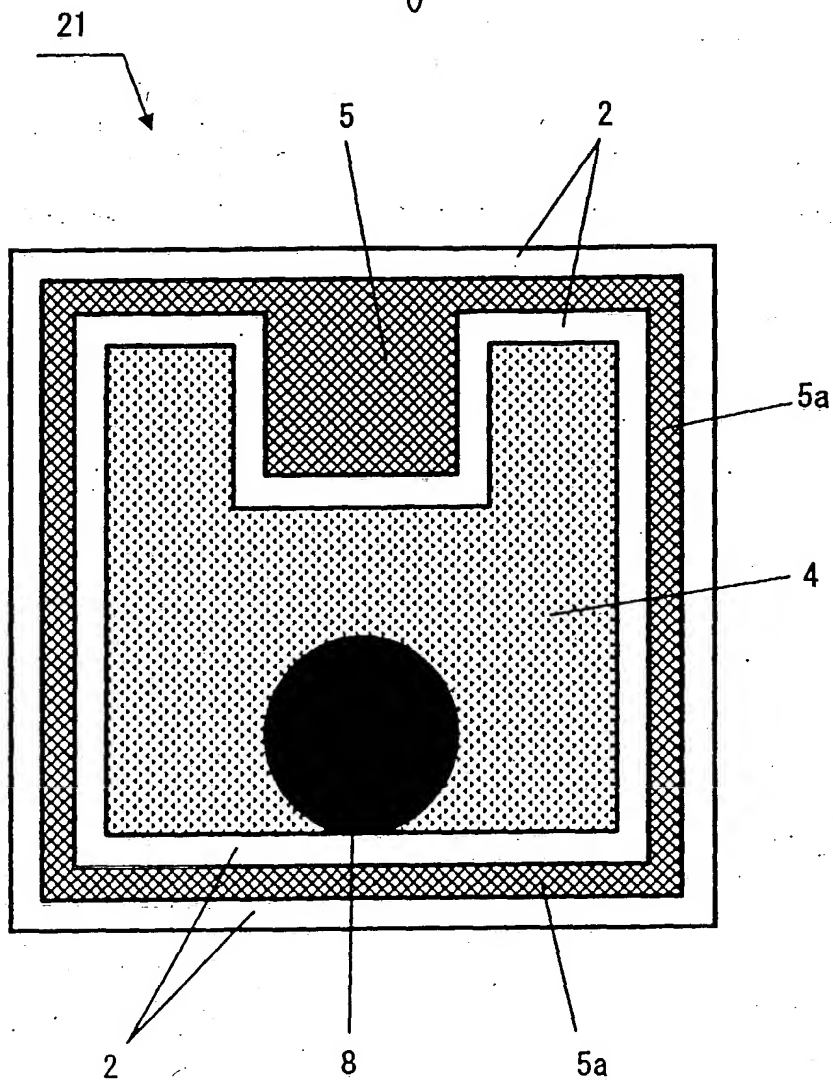


Fig-29

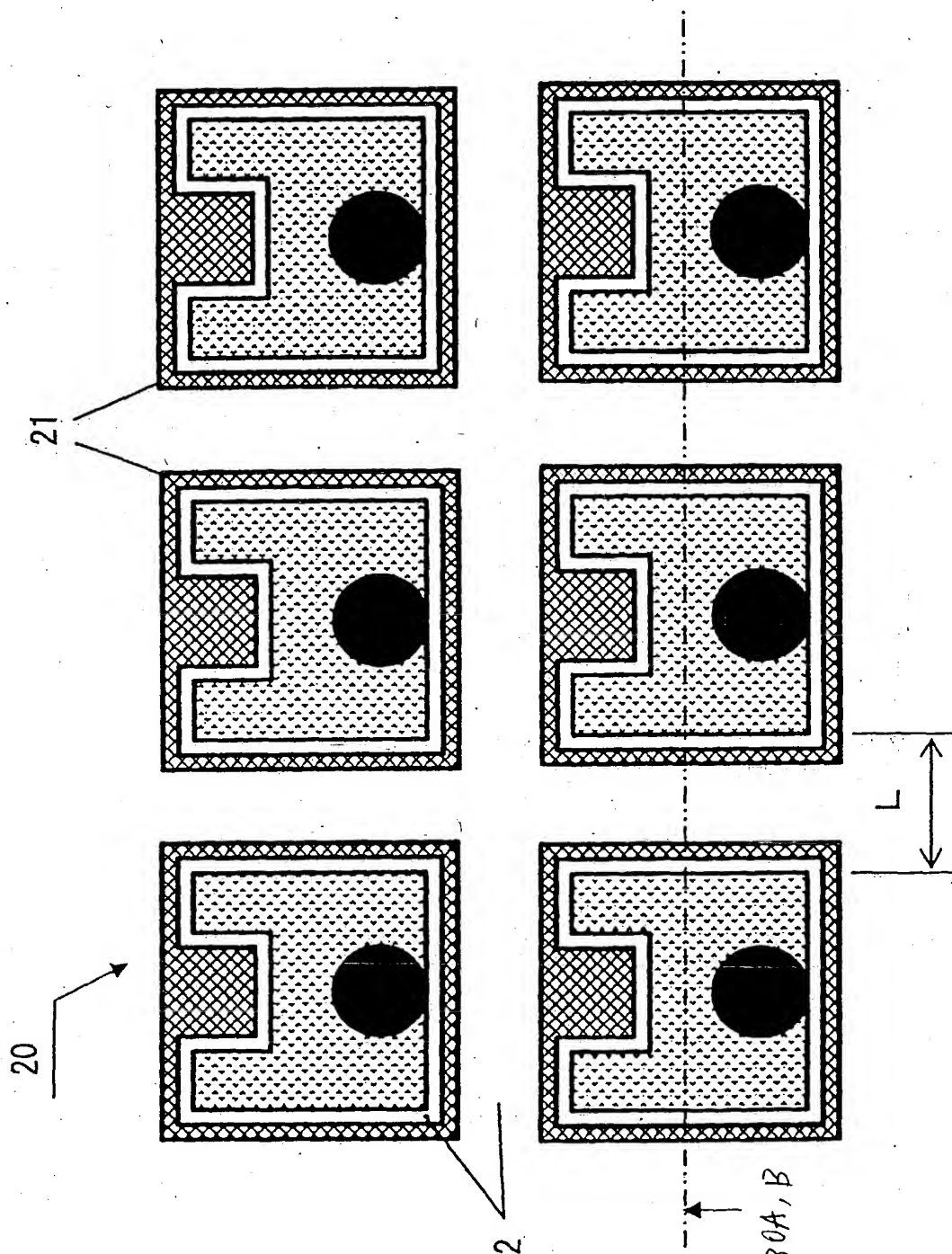


Fig. 30A

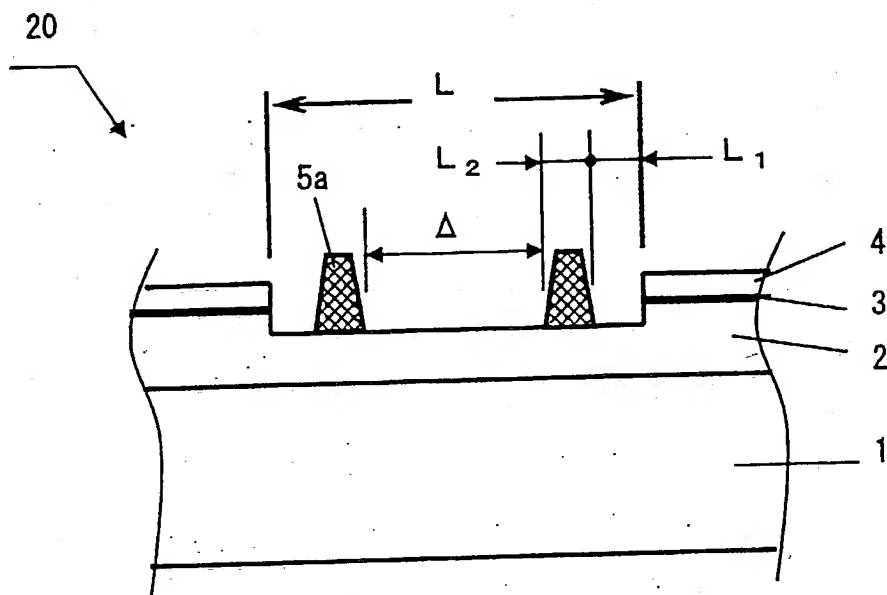


Fig. 30B

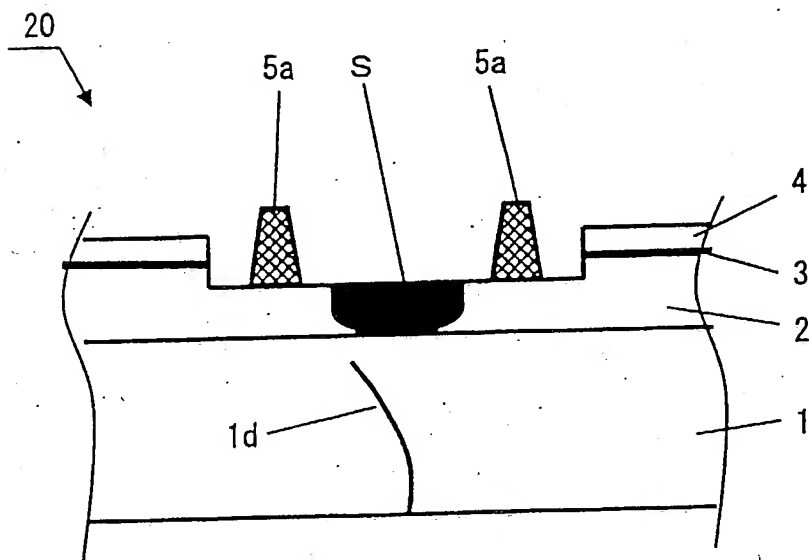


Fig. 31

